

GenX3[™] 1200V IGBTs w/ Diode

IXGK55N120A3H1 IXGX55N120A3H1

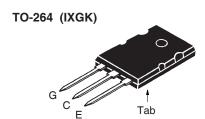
Ultra-Low-Vsat PT IGBTs for up to 3kHz Switching



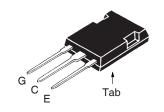
Symbol	Test Conditions	Maximum Ratings		
V _{CES}	T _J = 25°C to 150°C	1200	V	
V _{CGR}	$T_{_{\mathrm{J}}} = 25^{\circ}\mathrm{C}$ to 150°C, $R_{_{\mathrm{GE}}} = 1\mathrm{M}\Omega$	1200	V	
V _{GES}	Continuous	±20	V	
V _{GEM}	Transient	±30	V	
I _{C25}	T _c = 25°C (Chip Capability)	125	A	
I _{C110}	$T_{c} = 110^{\circ}C$	55	Α	
LRMS	T _C = 25°C (Lead RMS Limit)	120	Α	
I _{CM}	$T_{c} = 25^{\circ}C$, 1ms	400	Α	
SSOA	$V_{GE} = 15V, T_{VJ} = 125^{\circ}C, R_{G} = 3\Omega$	I _{CM} = 110	A	
(RBSOA)	Clamped Inductive Load	@ 0.8 • V _{CES}		
P _c	T _c = 25°C	460	W	
T _J		-55 +150	°C	
\mathbf{T}_{JM}		150	°C	
T_{stg}		-55 +150	°C	
T _L	Maximum Lead Temperature for Soldering	300	°C	
T _{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	°C	
M _d	Mounting Torque (IXGK)	1.13/10	Nm/lb.in.	
F _c	Mounting Force (IXGX)	20120/4.527	N/lb.	
Weight	TO-264	10	g	
	PLUS247	6	g	

Symbol (T _J = 25°C, U	Test Conditions Unless Otherwise Specified)	Chara Min.	cteristic Typ.	Value:	
$V_{GE(th)}$	$I_{\rm C}=1{\rm mA},V_{\rm CE}=V_{\rm GE}$	3.0		5.0	V
I _{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$			100	μA
	Note 1, $T_J = 125^{\circ}C$			2.0	mΑ
I _{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			±100	nA
V _{CE(sat)}	$I_{c} = I_{c110}, V_{GE} = 15V, \text{ Note 2}$ $T_{J} = 125^{\circ}\text{C}$		1.85 1.90	2.3	V

 $V_{CES} = 1200V$ $I_{C110} = 55A$ $V_{OS} \le 2.3V$



PLUS247™ (IXGX)



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- Optimized for Low Conduction Losses
- Anti-Parallel Ultra Fast Diode

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits



Symbol Test Conditions Characteristic (T _{.1} = 25°C, Unless Otherwise Specified) Min. Typ.			Values Max.	
$(1_{J} = 25 \text{ C},$			Тур.	
g _{fs}	$I_{\rm C} = I_{\rm C110}, V_{\rm CE} = 10V, \text{ Note 2}$	30	45	S
C _{ies}			4340	pF
C _{oes}	$V_{CE} = 25V, V_{GE} = 0V, f = 1 MHz$		300	pF
C _{res}			115	pF
$Q_{g(on)}$			185	nC
Q_{ge}	$I_{\rm C} = I_{\rm C110}, V_{\rm GE} = 15 \rm V, V_{\rm CE} = 0.5 \bullet \rm V_{\rm CES}$		25	nC
Q _{gc}			75	nC
t _{d(on)}			23	ns
t _{ri}	Inductive load, T _J = 25°C		42	ns
E _{on}	$I_{\rm C} = I_{\rm C110}, V_{\rm GE} = 15V$		5.1	mJ
t _{d(off)}	$V_{CE} = 0.8 \cdot V_{CES}, R_{G} = 3\Omega$		365	ns
t _{fi}	Note 3		282	ns
E _{off}			13.3	mJ
t _{d(on)}			24	ns
t _{ri}	Inductive load, T _J = 125°C		46	ns
E _{on}	$I_{\rm C} = I_{\rm C110}, V_{\rm GE} = 15V$		9.5	mJ
t _{d(off)}	$V_{CE} = 0.8 \cdot V_{CES}, R_{G} = 3\Omega$		618	ns
t _{fi}	Note 3		635	ns
E _{off}			29.0	mJ
R _{thJC}		·		0.27 °C/W
R _{thCK}			0.15	°C/W

Reverse Diode (FRED)

Symbo (T _J = 2		Test Conditions Unless Otherwise Specified)	Chara Min.	acteristic Typ.	Values Max.
V _F		$I_F = 60A$, $V_{GE} = 0V$, Note 2 $T_J = 150$ °C		1.85 1.90	2.5 V V
t _{rr}	$\overline{)}$	$I_F = 60A, V_{GE} = 0V,$		200	ns
I _{RM}	J	$-di_{F}/dt = 350A/\mu s, V_{R} = 600V, T_{J} = 100^{\circ}C$		24.6	A
R _{thJC}					0.42 °C/W

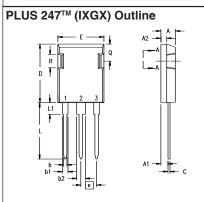
Notes:

- 1. Part must be heatsunk for high-temp Ices measurement.
- 2. Pulse test, $t \le 300 \mu s$, duty cycle, $d \le 2\%$.
- 3. Switching times & energy losses may increase for higher $V_{CE}(Clamp)$, T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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Terminals: 1 = Gate 2 = Collector 3 = Emitter

Dim.	Millimeter		Millimeter Inches		
	Min.	Max.	Min.	Max.	
Α	4.83	5.21	.190	.205	
A,	2.29	2.54	.090	.100	
A ₂	1.91	2.16	.075	.085	
b	1.14	1.40	.045	.055	
b₁	1.91	2.13	.075	.084	
b ₂	2.92	3.12	.115	.123	
С	0.61	0.80	.024	.031	
D	20.80	21.34	.819	.840	
Е	15.75	16.13	.620	.635	
е	5.45 BSC		.215	.215 BSC	
L	19.81	20.32	.780	.800	
L1	3.81	4.32	.150	.170	
Q	5.59	6.20	.220	0.244	
R	4.32	4.83	.170	.190	

